

ABSTRACT OF THE DISCLOSURE

A method for forming a trench isolation. A semiconductor substrate with an opening is provided, on which a mask layer is formed. A first insulating layer is conformably formed on
5 the semiconductor substrate and the trench, and the trench is filled with the first insulating layer. The first insulating layer is anisotropically etched to below the semiconductor substrate. A second insulating layer is formed on the semiconductor substrate and the trench. The second
10 insulating layer is planarized to expose the mask layer.